2SK3229

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

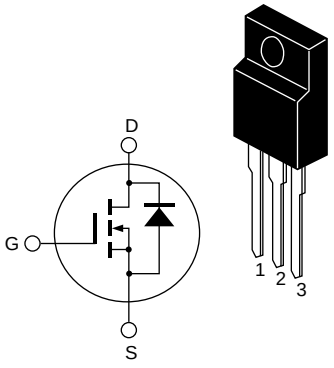
ADE-208-766(Z)
Target specification, 1st. Edition
Dec. 1, 1998

Features

- Low on-resistance
  $R_{DS(on)}$ =6mΩ typ.
- Low drive current
- 4V gate drive device can be driven from 5V source

Outline

TO–220CFM



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	80	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	60	A
Drain peak current	$I_{D(pulse)}$*[1]	240	A
Body-drain diode reverse drain current	I_{DR}	60	A
Avalanche current	I_{AP}*[3]	50	A
Avalanche energy	E_{AR}*[3]	181	mJ
Channel dissipation	Pch*[2]	35	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

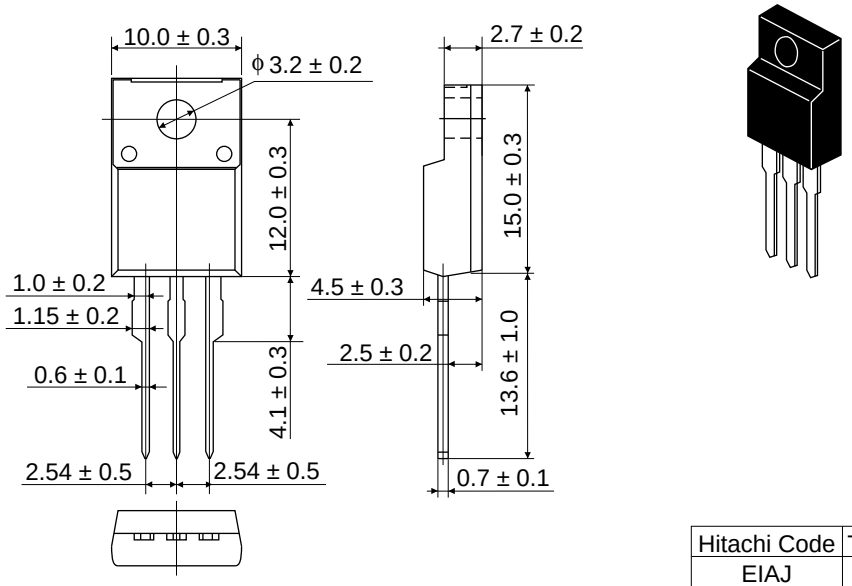
Note: 1. PW ≤ 10µs, duty cycle ≤ 1 %
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg ≥ 50Ω

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	80	—	—	V	I_D = 10mA, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.1	µA	V_{GS} = ±20V, V_{DS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	10	µA	V_{DS} = 80 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.5	V	I_D = 1mA, V_{DS} = 10V*[1]
Static drain to source on state	$R_{DS(on)}$	—	6.0	7.5	mΩ	I_D = 30A, V_{GS} = 10V*[1]
resistance		—	8.0	12	mΩ	I_D = 30A, V_{GS} = 4V*[1]
Forward transfer admittance	$\|y_{fs}\|$	50	85	—	S	I_D = 30A, V_{DS} = 10V*[1]
Input capacitance	Ciss	—	9700	—	pF	V_{DS} = 10V
Output capacitance	Coss	—	1250	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	290	—	pF	f = 1MHz
Total gate charge	Qg	—	150	—	nc	V_{DD} = 25V
Gate to source charge	Qgs	—	30	—	nc	V_{GS} = 25V
Gate to drain charge	Qgd	—	30	—	nc	I_D = 60A
Turn-on delay time	$t_{d(on)}$	—	80	—	ns	V_{GS} = 10V, I_D = 30A
Rise time	t_r	—	280	—	ns	R_L = 1Ω
Turn-off delay time	$t_{d(off)}$	—	780	—	ns	
Fall time	t_f	—	340	—	ns	
Body–drain diode forward voltage	V_{DF}	—	1.0	—	V	I_F = 60A, V_{GS} = 0
Body–drain diode reverse recovery time	t_{rr}	—	80	—	ns	I_F = 60A, V_{GS} = 0 diF/ dt =50A/µs

Note: 1. Pulse test

Package Dimensions (Unit: mm)



Hitachi Code	TO–220CFM
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HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL
NorthAmerica : http:semiconductor.hitachi.com/
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For further information write to:

Hitachi Semiconductor
(America) Inc.
2000 Sierra Point Parkway
Brisbane, CA 94005-1897
Tel: <1> (800) 285-1601
Fax: <1> (303) 297-0447

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX